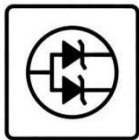


# MSKSEMI 美森科

SEMICONDUCTOR



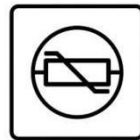
ESD



TVS



TSS



MOV



GDT



PLED

**SMDJ5.0(C)A -SMDJ220(C)A**

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**Product specification**

## Features

- For surface mounted applications in order to optimize board space
- Low profile package
- Built-in strain relief
- Glass passivated junction
- Low inductance
- Excellent clamping capability
- 3000W peak pulse power capability at 10/1000 $\mu$ s waveform, repetition rate (duty cycle): 0.01%
- Fast response time
- Typical  $I_R$  less than 1 $\mu$ A above 10V
- High Temperature soldering: 260 $^{\circ}$ C/10 seconds at terminals
- Plastic package has underwriters laboratory flammability 94V-0
- Meets MSL level 1, per J-STD-020
- Safety certification: UL
- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance


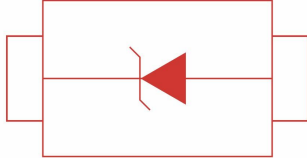

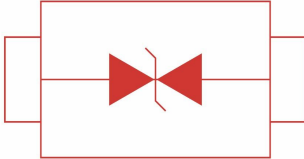
## Mechanical Data

- Case: JEDEC DO-214AB. Molded plastic over glass passivated junction
- Terminal: Tin plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode except bi-directional models
- Standard Packaging: 16mm tape (EIA STD RS-481)
- Weight: 0.28g

## Applications

- I/O interface
- AC/DC power supply
- Low frequency signal transmission line (RS232, RS485, etc.)

## Reference News

PACKAGE OUTLINE	PIN CONFIGURATION
	
<b>SMC(DO-214AB) Unipolar</b>	
	
<b>SMC(DO-214AB) Bipolar</b>	

**Ratings at 25°C ambient temperature unless otherwise specified.**

Rating	Symbol	Value	Units
Peak pulse power dissipation at 10/1000μs waveform (Note1, Note2, Fig.1)	P <sub>PPM</sub>	Minimum 3000	Watts
Peak pulse current of at 10/1000μs waveform (Note 1, Fig.3)	I <sub>PPM</sub>	See Table	Amps
Steady state power dissipation at T <sub>A</sub> =50°C (Fig.5)	P <sub>M(AV)</sub>	6.5	Watts
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load, (JEDEC Method) (Note3, Fig.6)	I <sub>FSM</sub>	300	Amps
Operating junction and Storage Temperature Range.	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C
Typical thermal resistance junction to lead	R <sub>θJL</sub>	15	°C/W
Typical thermal resistance junction to ambient	R <sub>θJA</sub>	75	°C/W

**Notes:** 1. Non-repetitive current pulse, per Fig.3 and derated above T<sub>A</sub>=25°C per Fig.2.

2. Mounted on 8.0mm×8.0mm copper pads to each terminal.

3. 8.3ms single half sine-wave, or equivalent square wave, duty cycle=4 pulses per minutes maximum.

**Electrical Characteristics (TA=25°C)**

Part Number		Device Marking Code		Reverse Stand-Off Voltage	Breakdown Voltage @I <sub>r</sub>	Test Current	Maximum Clamping Voltage @I <sub>PP</sub>	Peak Pulse Current	Reverse Leakage @ V <sub>RWM</sub>
Unidirectional	Bidirectional	UNI	BI	V <sub>RWM</sub> (V)	V <sub>BR</sub> (V)	I <sub>r</sub> (mA)	V <sub>c</sub> (V)	I <sub>PP</sub> (A)	I <sub>r</sub> (μA)
SMDJ5.0A	SMDJ5.0CA	RDE	DDE	5.0	6.40~7.00	10	9.2	326.1	800
SMDJ6.0A	SMDJ6.0CA	RDG	DDG	6.0	6.67~7.37	10	10.3	291.3	800
SMDJ6.5A	SMDJ6.5CA	RDK	DDK	6.5	7.22~7.98	10	11.2	267.9	500
SMDJ7.0A	SMDJ7.0CA	PDM	DDM	7.0	7.78~8.60	10	12.0	250.0	200
SMDJ7.5A	SMDJ7.5CA	PDP	DDP	7.5	8.33~9.21	1	12.9	232.6	100
SMDJ8.0A	SMDJ8.0CA	PDR	DDR	8.0	8.89~9.83	1	13.6	220.6	50
SMDJ8.5A	SMDJ8.5CA	PDT	DDT	8.5	9.44~10.40	1	14.4	208.3	20
SMDJ9.0A	SMDJ9.0CA	PDV	DDV	9.0	10.00~11.10	1	15.4	194.8	10
SMDJ10A	SMDJ10CA	PDX	DDX	10.0	11.10~12.30	1	17.0	176.5	5
SMDJ11A	SMDJ11CA	PDZ	DDZ	11.0	12.20~13.50	1	18.2	164.8	2
SMDJ12A	SMDJ12CA	PEE	DEE	12.0	13.30~14.70	1	19.9	150.8	2
SMDJ13A	SMDJ13CA	PEG	DEG	13.0	14.40~15.90	1	21.5	139.5	2
SMDJ14A	SMDJ14CA	PEK	DEK	14.0	15.60~17.20	1	23.2	129.3	2
SMDJ15A	SMDJ15CA	PEM	DEM	15.0	16.70~18.50	1	24.4	123.0	2
SMDJ16A	SMDJ16CA	PEP	DEP	16.0	17.80~19.70	1	26.0	115.4	2
SMDJ17A	SMDJ17CA	PER	DER	17.0	18.90~20.90	1	27.6	108.7	2
SMDJ18A	SMDJ18CA	PET	DET	18.0	20.00~22.10	1	29.2	102.7	2
SMDJ20A	SMDJ20CA	PEV	DEV	20.0	22.20~24.50	1	32.4	92.6	2
SMDJ22A	SMDJ22CA	PEX	DEX	22.0	24.40~26.90	1	35.5	84.5	2
SMDJ24A	SMDJ24CA	PEZ	DEZ	24.0	26.70~29.50	1	38.9	77.1	2

Part Number		Device Marking Code		Reverse Stand-Off Voltage	Breakdown Voltage @ $I_T$	Test Current	Maximum Clamping Voltage @ $I_{PP}$	Peak Pulse Current	Reverse Leakage @ $V_{RWM}$
Unidirectional	Bidirectional	UNI	BI	$V_{RWM}(V)$	$V_{BR}(V)$	$I_T(mA)$	$V_C(V)$	$I_{PP}(A)$	$I_R(\mu A)$
SMDJ26A	SMDJ26CA	PFE	DFE	26.0	28.90~31.90	1	42.1	71.3	2
SMDJ28A	SMDJ28CA	PFG	DFG	28.0	31.10~34.40	1	45.4	66.1	2
SMDJ30A	SMDJ30CA	PFK	DFK	30.0	33.30~36.80	1	48.4	62.0	2
SMDJ33A	SMDJ33CA	PFM	DFM	33.0	36.70~40.60	1	53.3	56.3	2
SMDJ36A	SMDJ36CA	PFP	DFP	36.0	40.00~44.20	1	58.1	51.6	2
SMDJ40A	SMDJ40CA	PFR	DFR	40.0	44.40~49.10	1	64.5	46.5	2
SMDJ43A	SMDJ43CA	PFT	DFT	43.0	47.80~52.80	1	69.4	43.2	2
SMDJ45A	SMDJ45CA	PFV	DFV	45.0	50.00~55.30	1	72.7	41.3	2
SMDJ48A	SMDJ48CA	PFX	DFX	48.0	53.30~58.90	1	77.4	38.8	2
SMDJ51A	SMDJ51CA	PFZ	DFZ	51.0	56.70~62.70	1	82.4	36.4	2
SMDJ54A	SMDJ54CA	PGE	DGE	54.0	60.00~66.30	1	87.1	34.4	2
SMDJ58A	SMDJ58CA	PGG	DGG	58.0	64.40~71.20	1	93.6	32.1	2
SMDJ60A	SMDJ60CA	PGK	DGK	60.0	66.70~73.70	1	96.8	31.0	2
SMDJ64A	SMDJ64CA	PGM	DGM	64.0	71.10~78.60	1	103.0	29.1	2
SMDJ70A	SMDJ70CA	PGP	DGP	70.0	77.80~86.00	1	113.0	26.5	2
SMDJ75A	SMDJ75CA	PGR	DGR	75.0	83.30~92.10	1	121.0	24.8	2
SMDJ78A	SMDJ78CA	PGT	DGT	78.0	86.70~95.80	1	126.0	23.8	2
SMDJ85A	SMDJ85CA	PGV	DGV	85.0	94.40~104.00	1	137.0	21.9	2
SMDJ90A	SMDJ90CA	PGX	DGX	90.0	100.00~111.00	1	146.0	20.5	2
SMDJ100A	SMDJ100CA	PGZ	DGZ	100.0	111.00~123.00	1	162.0	18.5	2
SMDJ110A	SMDJ110CA	PHE	DHE	110.0	122.00~135.00	1	177.0	16.9	2
SMDJ120A	SMDJ120CA	PHG	DHG	120.0	133.00~147.00	1	193.0	15.5	2
SMDJ130A	SMDJ130CA	PHK	DHK	130.0	144.00~159.00	1	209.0	14.4	2
SMDJ150A	SMDJ150CA	PHM	DHM	150.0	167.00~185.00	1	243.0	12.3	2
SMDJ160A	SMDJ160CA	PHP	DHP	160.0	178.00~197.00	1	259.0	11.6	2
SMDJ170A	SMDJ170CA	PHR	DHR	170.0	189.00~209.00	1	275.0	10.9	2
SMDJ180A	SMDJ180CA	HHT	IHT	180.0	201.00~222.00	1	292.0	10.3	2
SMDJ190A	SMDJ190CA	HHV	IHV	190.0	211.00~233.00	1	308.0	9.7	2
SMDJ200A	SMDJ200CA	HHX	IHX	200.0	224.00~247.00	1	324.0	9.3	2
SMDJ210A	SMDJ210CA	HHZ	IHZ	210.0	237.00~263.00	1	340.0	8.8	2
SMDJ220A	SMDJ220CA	HIE	IIE	220.0	246.00~272.00	1	356.0	8.4	2

**Ratings and Characteristic Curves (TA=25°C unless otherwise noted)**

Figure 1. Peak Pulse Power Rating Curve

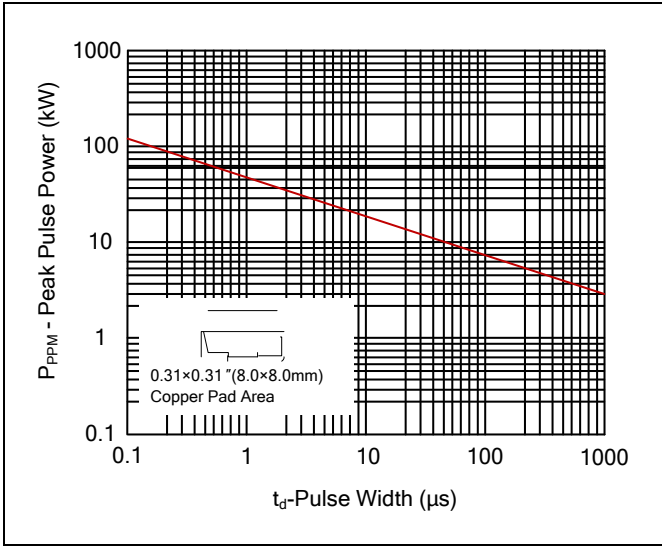


Figure 2. Pulse Derating Curve

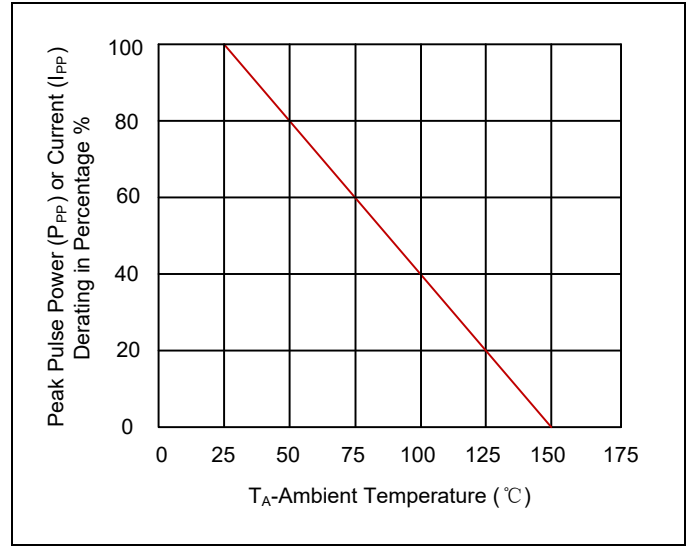


Figure 3. Pulse Waveform

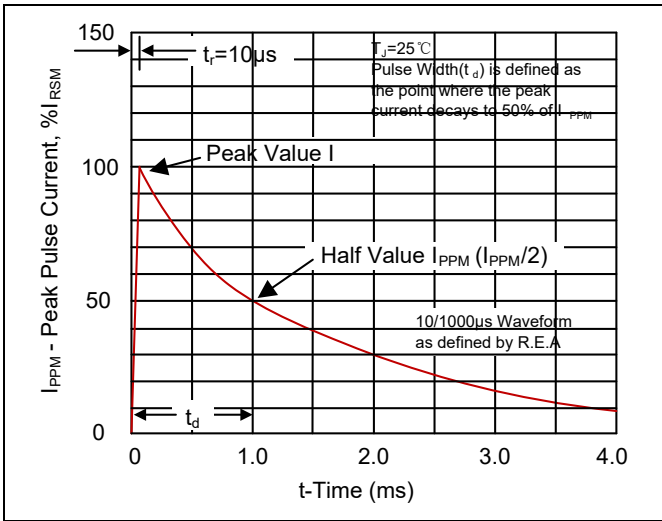


Figure 4. Typical Junction Capacitance

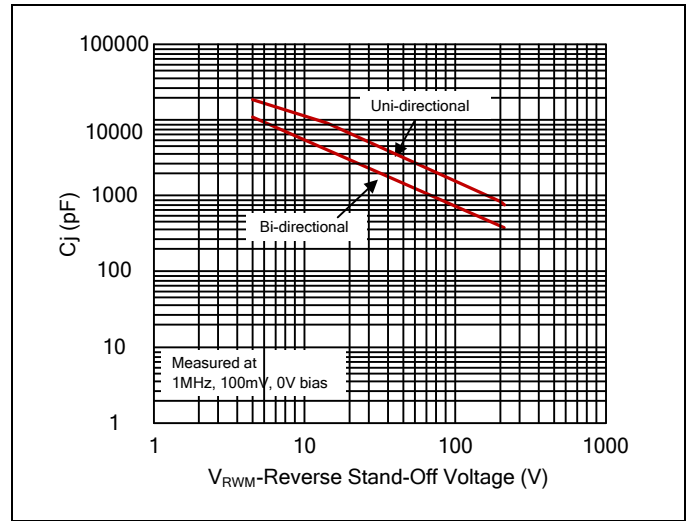


Figure 5. Steady State Power Dissipation Derating Curve

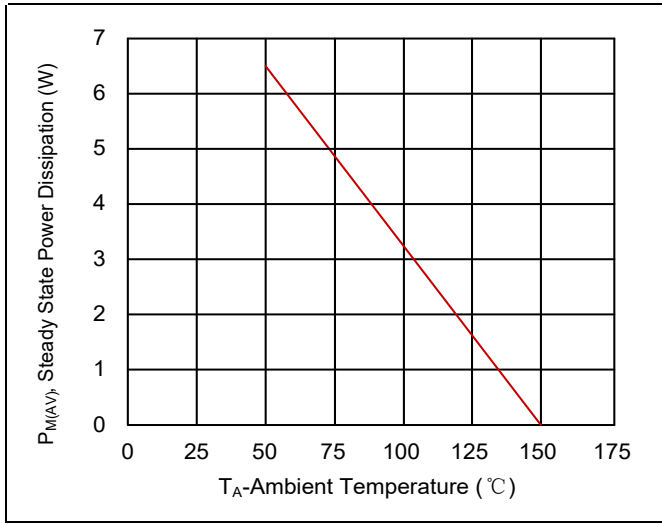
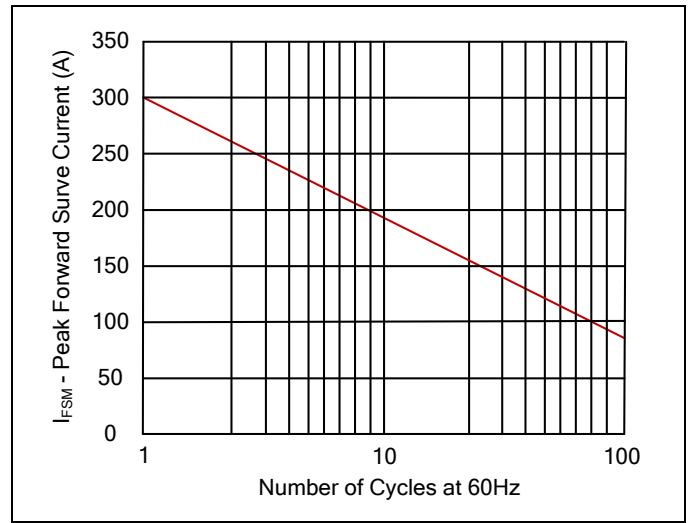
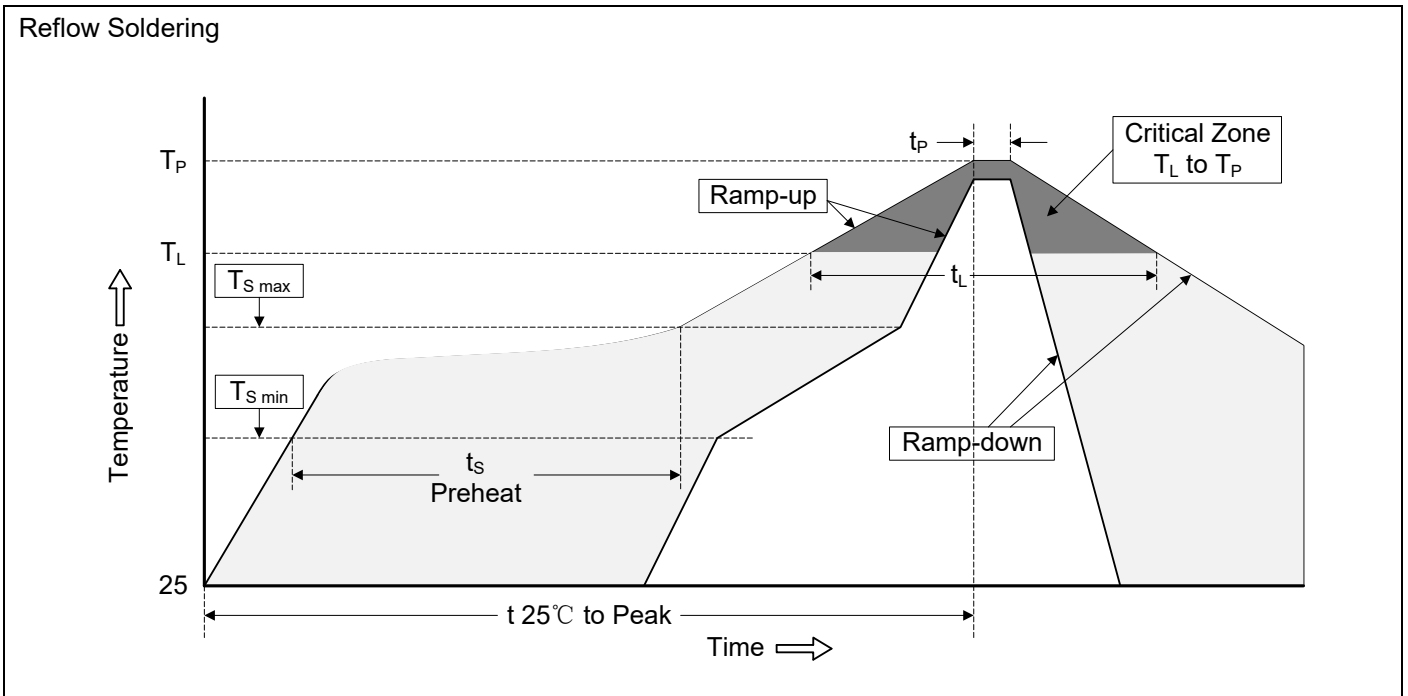


Figure 6. Maximum Non-Repetitive Forward Surge Current Uni-Directional Only



**Recommended Soldering Conditions**

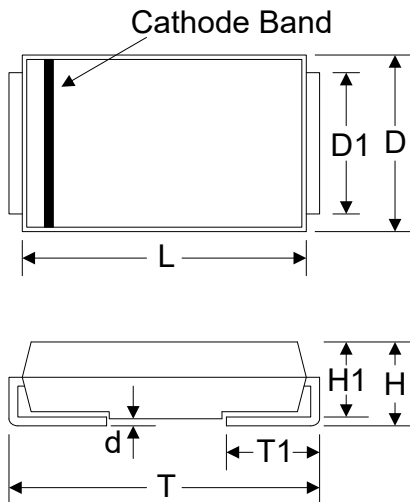


Recommended Conditions

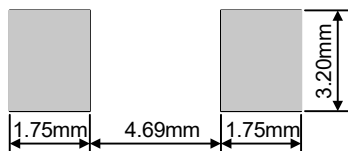
Profile Feature	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	3°C/second max.
Preheat -Temperature Min ( $T_{S\ min}$ ) -Temperature Max ( $T_{S\ max}$ ) -Time (min to max) ( $t_s$ )	150°C 200°C 60-180 seconds
$T_{S\ max}$ to $T_L$ -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature ( $T_L$ ) -Time ( $t_L$ )	217°C 60-150 seconds
Peak Temperature ( $T_P$ )	260°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Dimensions (SMC/DO-214AB)

Product:



Pad:



Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
L	6.60	7.11	0.	0.
D	5.59	6.22	2600.	2800.
D1	2.90	3.20	2200.	2450.
T	7.75	8.13	1140.	1260.
T1	0.76	1.52	3050.	3200.
d	-	0.203	030	0600.
H	2.20	2.80	0.087	0080.
H1	2.06	2.62	0.079	0.103

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